

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	FinFET near10 (source near5 drain near5 channel)	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/03 18:46

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	109099	OSI and substrate near5 silicon adj carbide and dielectric layer and gate and insulat\$3	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/03 17:54
L2	109112	SOI and substrate near5 silicon adj carbide and dielectric layer and gate and insulat\$3	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/03 17:54
L3	109119	SOI and substrate near5 (silicon adj carbide) and dielectric layer and gate and insulat\$3	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/03 17:55
L4	12	SOI and substrate near5 (silicon adj carbide) and dielectric adj layer and gate and insulat\$3	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/12/03 17:55